

SANYO	No.3775A	2SK1474
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

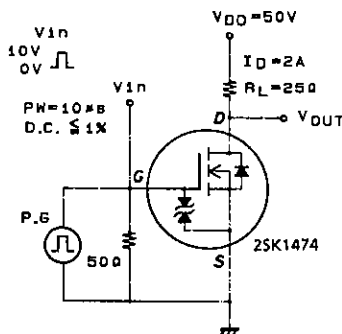
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V _{DS}	100	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current(DC)	I _D	4	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	16 A
Allowable Power Dissipation	P _D	Tc = 25°C	20 W
Channel Temperature	T _{ch}		150 °C
Storage Temperature	T _{stg}		- 55 to +150 °C

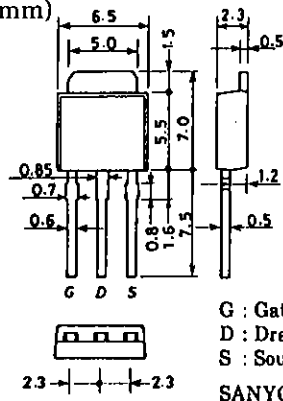
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	100			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±15			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0			100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, I _D = 2A	2.5	4		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = 2A, V _{GS} = 10V		0.3	0.4	Ω
	R _{DS(on)}	I _D = 2A, V _{GS} = 4V		0.4	0.55	Ω
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz		380		pF
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz		80		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz		15		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	"		13		ns
Turn-OFF Delay Time	t _{d(off)}	"		70		ns
Fall Time	t _f	"		30		ns
Diode Forward Voltage	V _{SD}	I _S = 4A, V _{GS} = 0	1.0	1.5		V

Switching Time Test Circuit

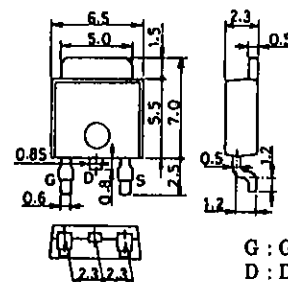


Package Dimensions 2083A (unit : mm)

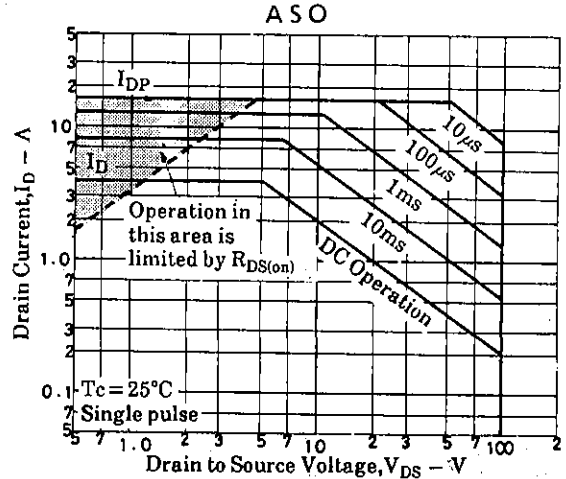
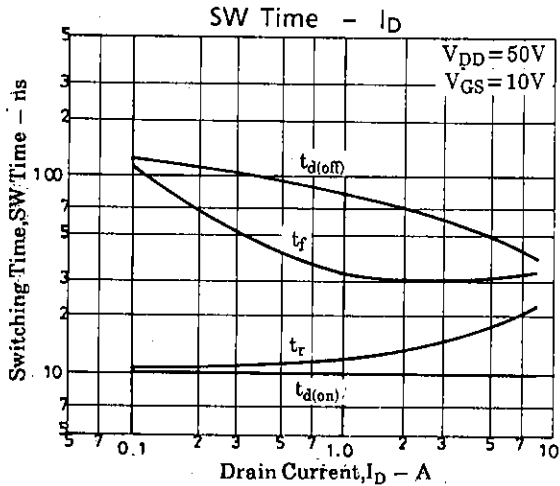
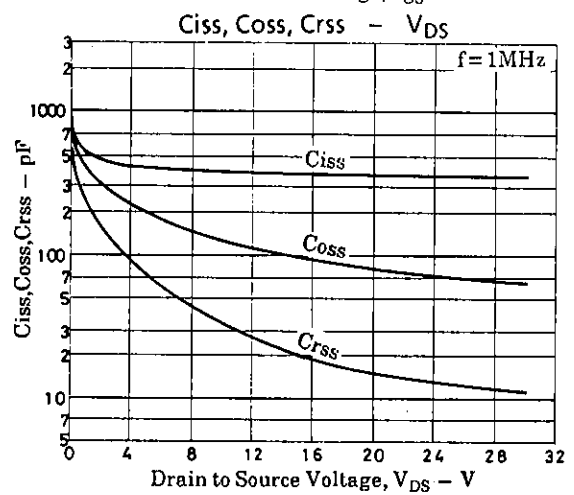
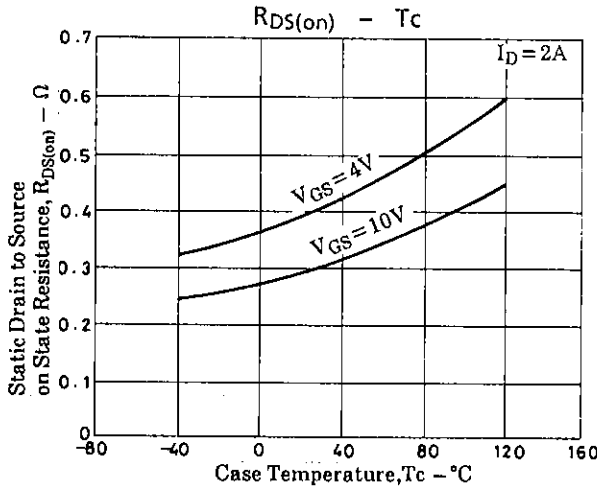
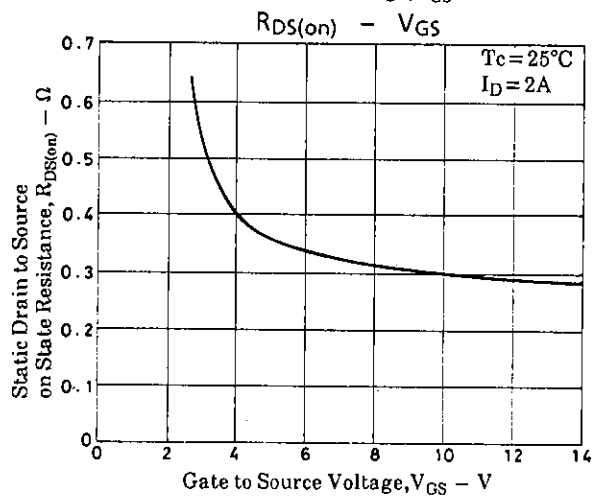
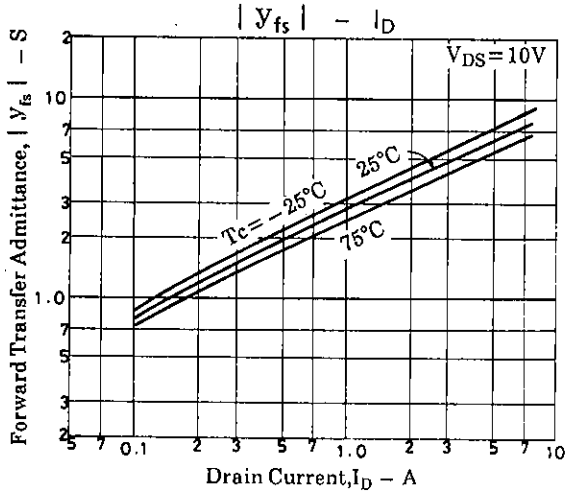
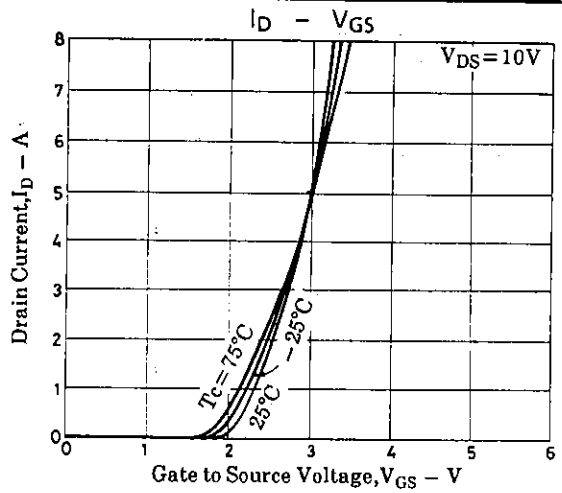
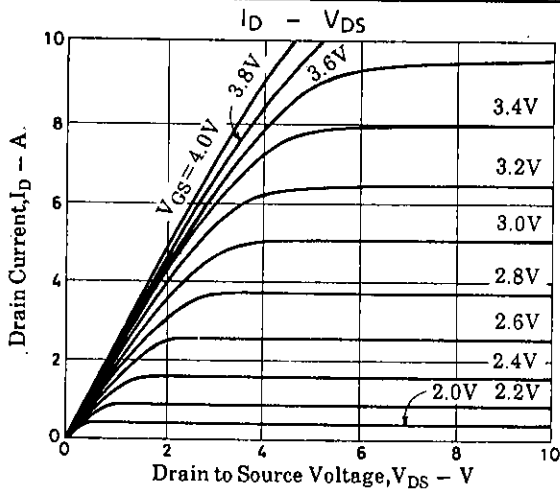


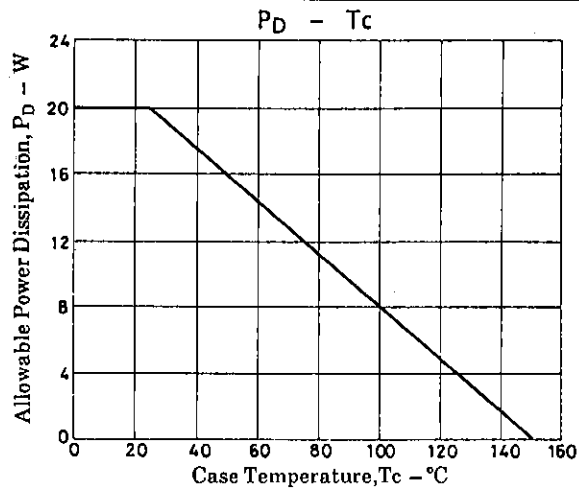
G : Gate
D : Drain
S : Source
SANYO : TP

Package Dimensions 2092A (unit : mm)



G : Gate
D : Drain
S : Source
SANYO : TP-FA





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